

P-Channel Enhancement Mode Power MOSFET

Description

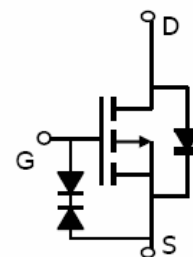
The PE3415 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

General Features

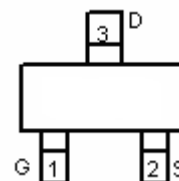
- $V_{DS} = -20V, I_D = -4.5A$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 47m\Omega @ V_{GS} = -4.5V$
ESD Rating: 2500V HBM
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM application
- Load switch



Schematic diagram



Marking and pin Assignment



SOT-23-3 top view

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-4.5	A
Drain Current-Pulsed (Note 1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20		-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.65	-1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4A	-	34.	47	mΩ
		V _{GS} =-2.5V, I _D =-4A	-	44	60	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4A	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-10V, V _{GS} =0V, F=1.0MHz	-	950	-	PF
Output Capacitance	C _{OSS}		-	165	-	PF
Reverse Transfer Capacitance	C _{rss}		-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, R _L =2. 5Ω V _{GS} =-4.5V, R _{GEN} =3Ω	-	12		nS
Turn-on Rise Time	t _r		-	10		nS
Turn-Off Delay Time	t _{d(off)}		-	19		nS
Turn-Off Fall Time	t _f		-	25		nS
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-4A, V _{GS} =-4.5V	-	12		nC
Gate-Source Charge	Q _{gs}		-	1.4	-	nC
Gate-Drain Charge	Q _{gd}		-	3.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-2.2	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

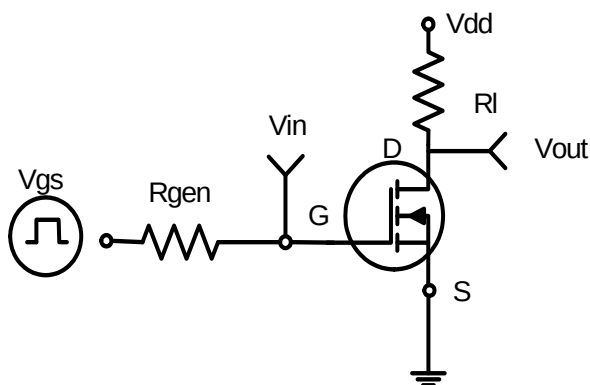


Figure 1: Switching Test Circuit

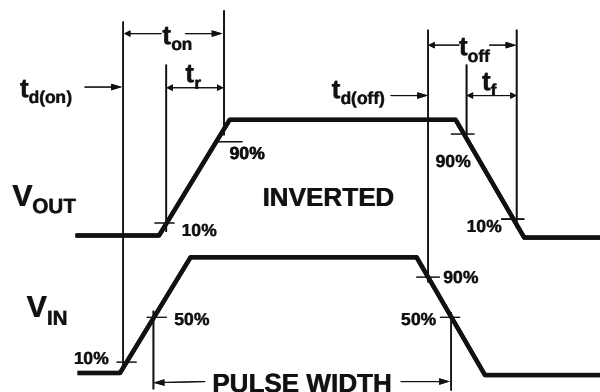


Figure 2: Switching Waveforms

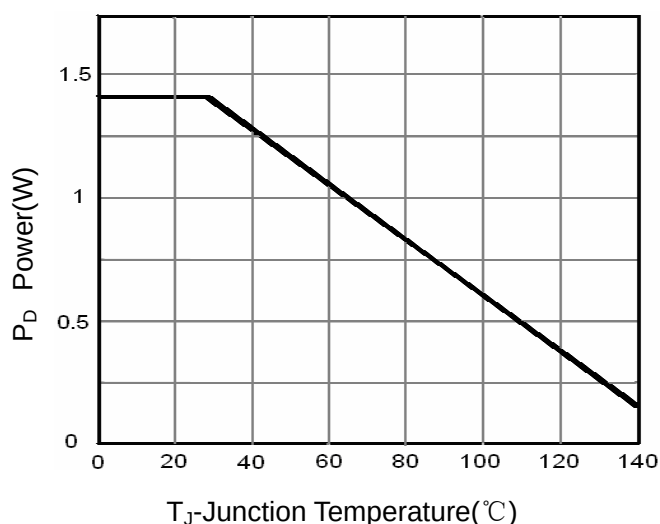


Figure 3 Power Dissipation

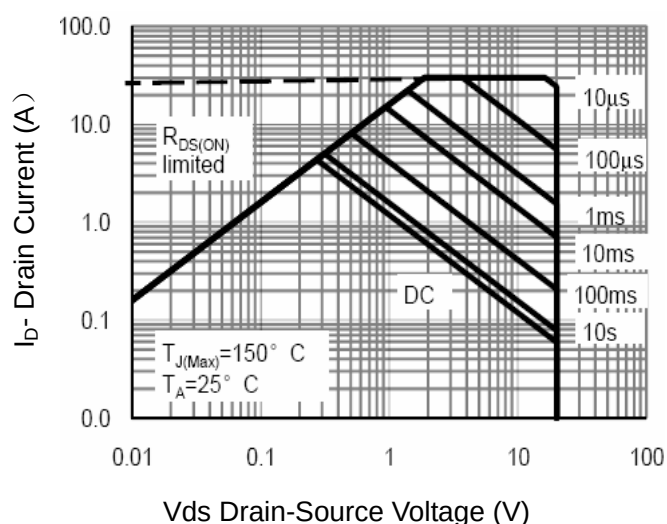


Figure 4 Safe Operation Area

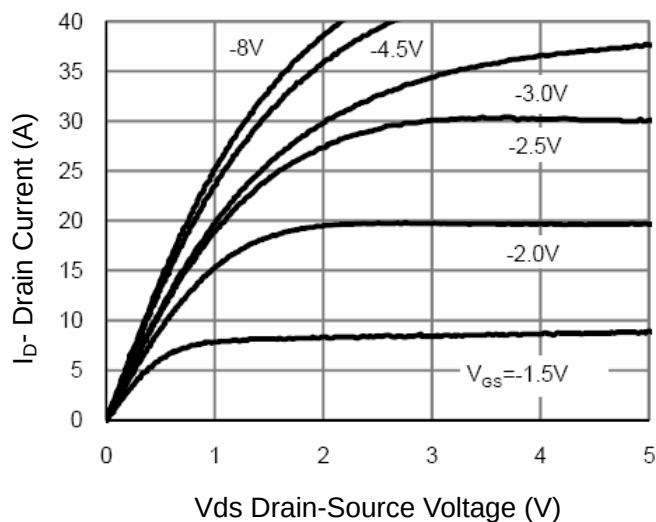


Figure 5 Output CHARACTERISTICS

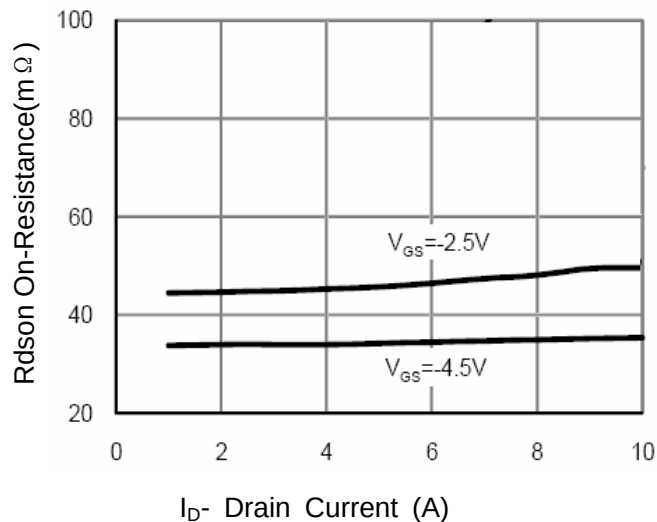


Figure 6 Drain-Source On-Resistance

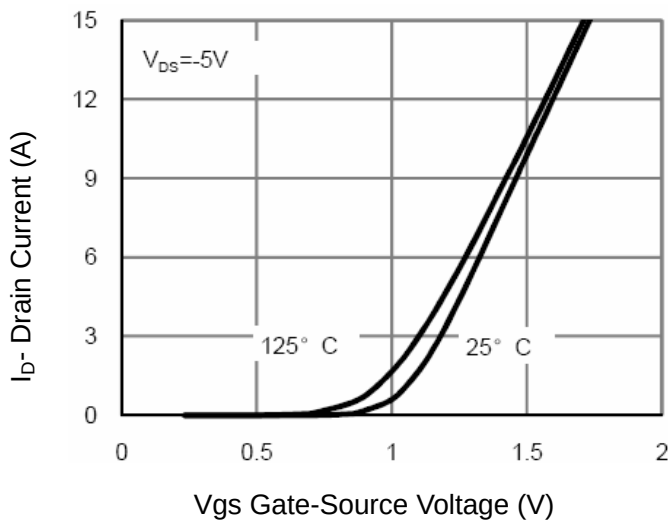


Figure 7 Transfer Characteristics

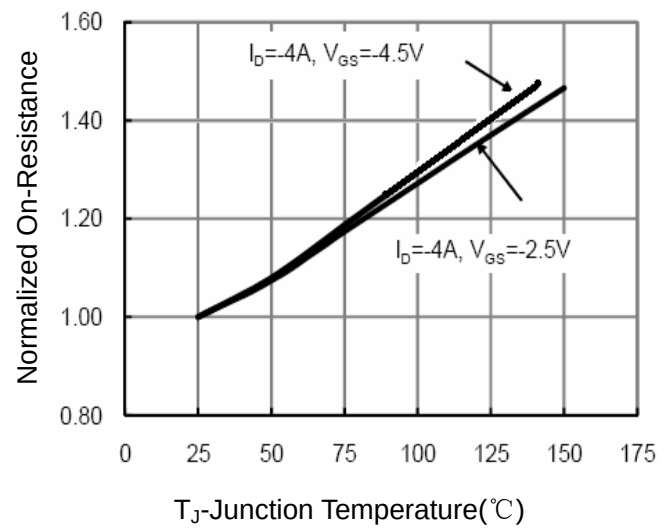


Figure 8 Drain-Source On-Resistance

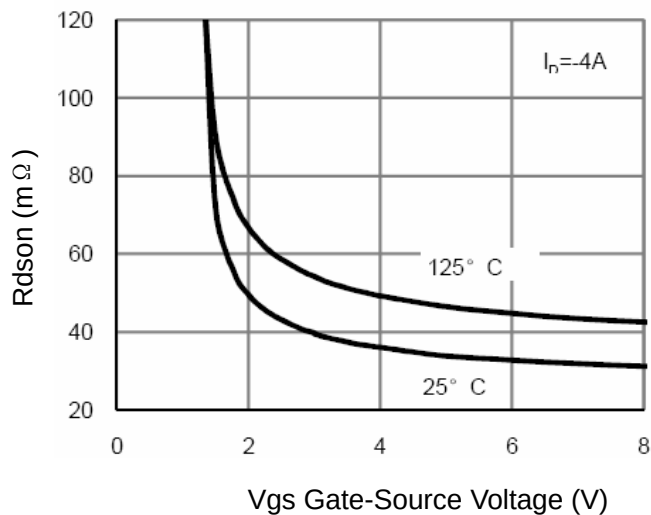


Figure 9 $R_{DS(on)}$ vs V_{GS}

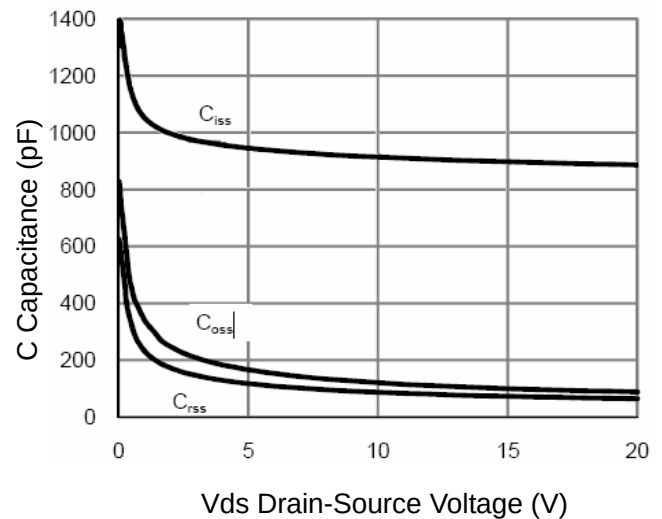


Figure 10 Capacitance vs V_{DS}

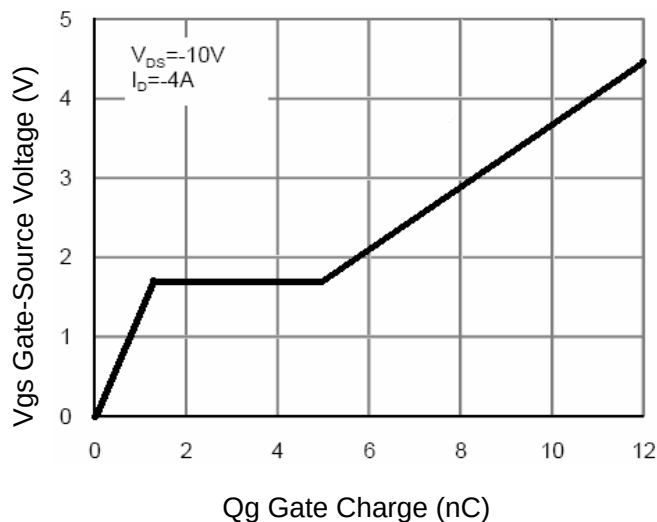


Figure 11 Gate Charge

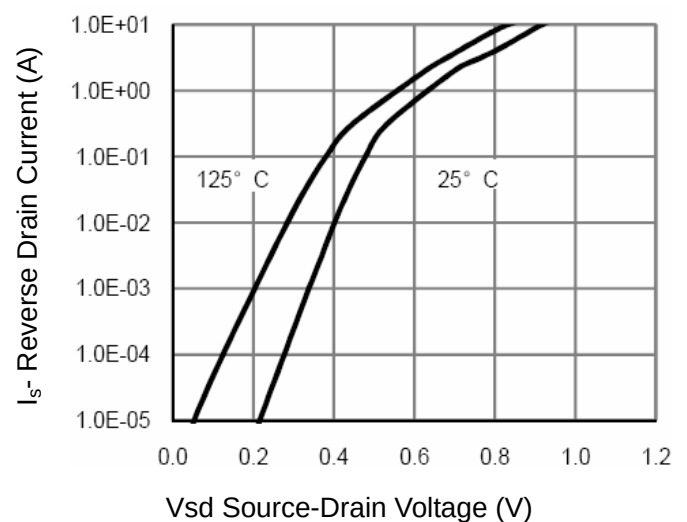


Figure 12 Source- Drain Diode Forward

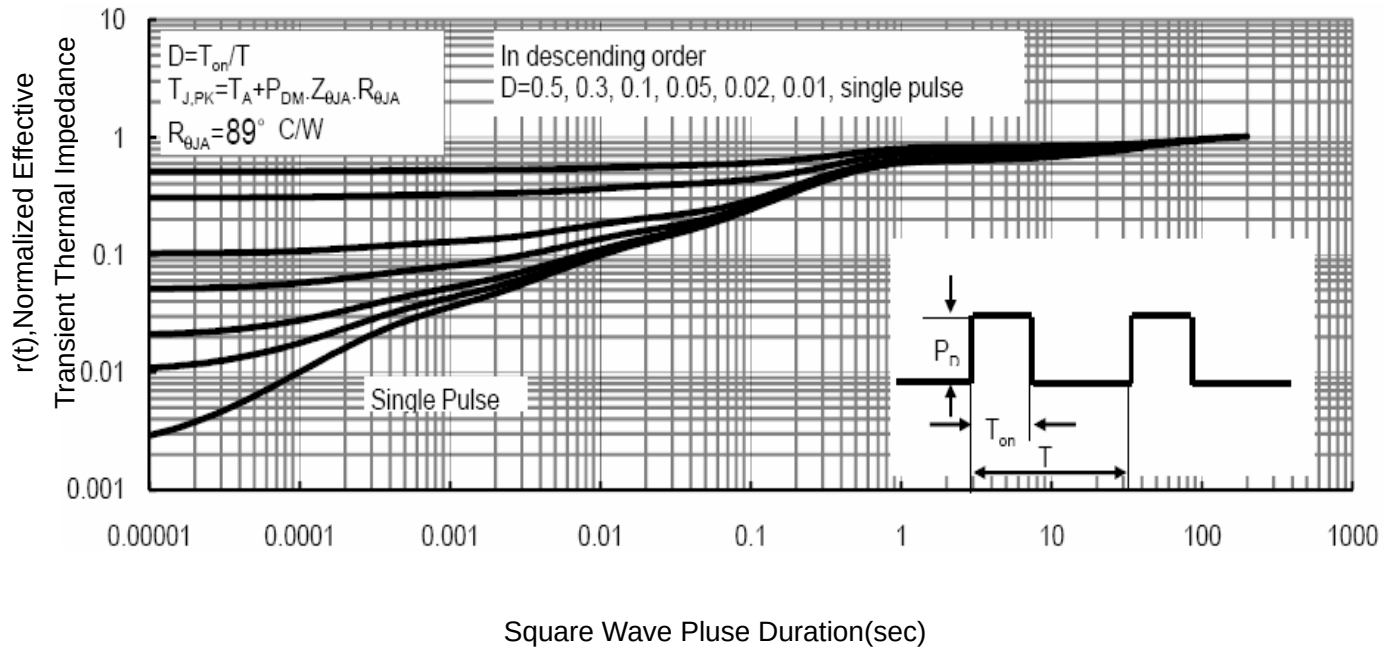
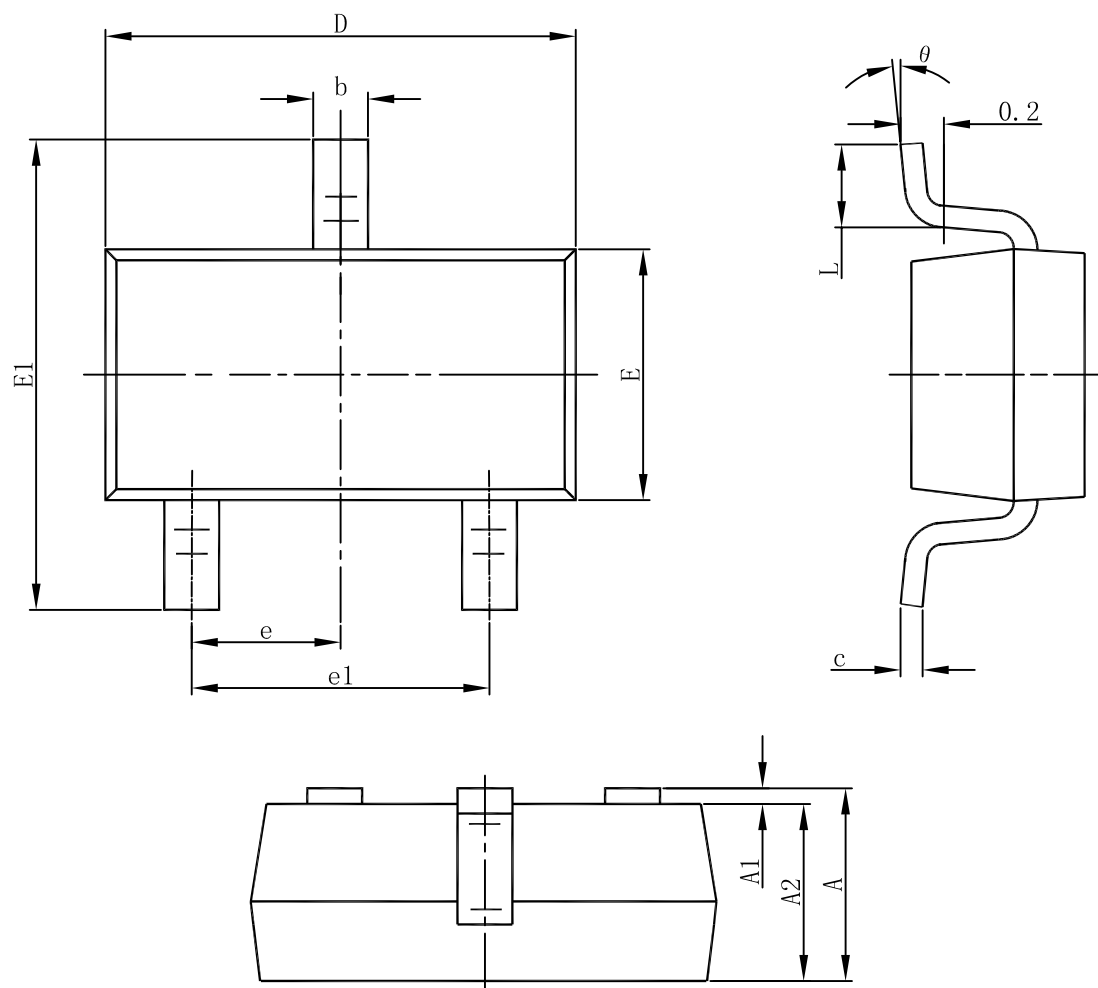


Figure 13 Normalized Maximum Transient Thermal Impedance

SOT-23-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°